

LOW LEAKAGE CURRENT STATIC RANDOM ACCESS MEMORY

Abstract

A static random access memory (SRAM) has a plurality of SRAM cells, a first switch unit, a second switch unit, and a capacitor.

During read/write operations of the SRAM cells, the first switch unit and the second switch unit are turned on so that two power terminals of the SRAM cells respectively electrically connect to V_{DD} and V_{SS} and that the capacitor electrically connects between V_{DD} and V_{SS} . When the SRAM cells are not accessed, the first switch unit and the second switch unit are turned off and the capacitor keeps a voltage gap between the two power terminals of the SRAM cells greater than a predetermined value.